

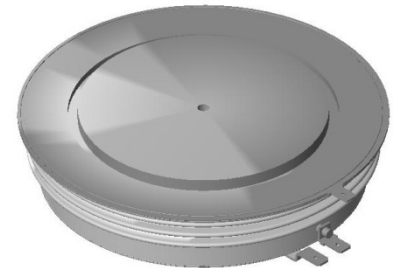
Press-pack IGBT's

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With a track record spanning more than 10 years as a leading innovator in press-pack IGBT technology, IXYS UK is proud to offer their range of 2.5kV and 4.5kV devices featuring the latest generation chipset offering improved SOA

This advanced technology is based on an enhanced planar cell design featuring the latest carrier enhancement techniques. Delivering comparable VCE(sat) to modern trench designs whilst retaining the superior RBSOA, SCSOA performance and easy driving characteristics of traditional planar technology

When combined with IXYS UK's proven hermetic press-pack technology, these devices re-define the state-of-the-art for high power switching devices



Features and benefits

- Bondless construction for improved reliability
- Hermetic devices suitable for all cooling options including direct liquid immersion
- Explosion and rupture safe
- High thermal cycling resistance
- Double side cooling
- Mechanically compatible with GTO thyristors, allowing upgrading of existing equipment and designs to new IGBT technology

Applications



- Medium voltage drives
 - Marine drives
 - Traction
 - Wind power converters
 - Industrial
- Energy utilities
 - STATCOM
 - FACTS
 - Active VAR controllers
 - Renewable generation



Product Brief – Press-pack IGBT's

In a range of packages with electrode diameters of up to 125mm, IXYS UK have both reverse conducting and asymmetric blocking types available

An improved diode chip complements the IGBT and offers breakthrough levels of performance. Choice of diode to IGBT ratio enabling full utilisation of the IGBT in reverse conducting applications

New third generation HP-sonic monolithic diode range complements our new asymmetric IGBT range and also supports such applications as multi-level diode clamped converters

Press-pack IGBT's are now gaining significant market share in the high performance medium voltage drive sector in the 2MW to 30MW range. They offer all the benefits of conventional IGBT's and more, over alternative bipolar technology while maintaining the high reliability levels associated with press-pack devices in these systems

Type Part No.	V_{CES} V	I_C A	$V_{CE(sat)}$ $I_C=I_C$ V	Reverse Conducting	V_F $I_F=I_C$ V	T_{JM} °C	Outline
T0160NB45A	4500	160	3.45	Yes	4.00	125	Fig 1
T0240NB45E	4500	240	3.70	No	N/A	125	Fig 1
T0340VB45G	4500	340	3.60	Yes	3.50	125	Fig 2
T0360NB25A	2500	360	2.95	Yes	2.25	125	Fig 1
T0500NB25E	2500	500	2.90	No	N/A	125	Fig 1
T0510VB45E	4500	510	3.60	No	N/A	125	Fig 2
T0570VB25G	2500	570	2.95	Yes	2.05	125	Fig 2
T0600TB45A	4500	600	3.70	Yes	3.90	125	Fig 3
T0800EB45G	4500	800	3.60	Yes	3.50	125	Fig 4
T0800TB45E	4500	800	3.60	No	N/A	125	Fig 3
T0850VB25E	2500	850	2.90	No	N/A	125	Fig 2
T0900EB45A	4500	900	3.70	Yes	3.90	125	Fig 4
T1200TB25A	2500	1200	3.00	Yes	2.50	125	Fig 3
T1200EB45E	4500	1200	3.60	No	N/A	125	Fig 4
T1500TB25E	2500	1500	2.90	No	N/A	125	Fig 3
T1600GB45G	4500	1600	3.60	Yes	3.50	125	Fig 6
T1800GB45A	4500	1800	3.70	Yes	3.90	125	Fig 6
T2250AB25E	2500	2250	2.90	No	N/A	125	Fig 5
T2400GB45E	4500	2400	3.60	No	N/A	125	Fig 6

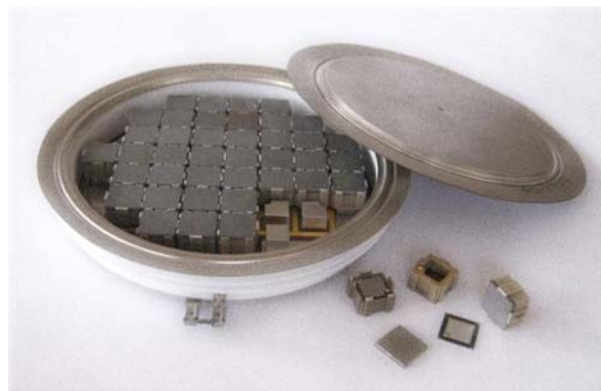


Figure 1 – 47mm \varnothing pole face

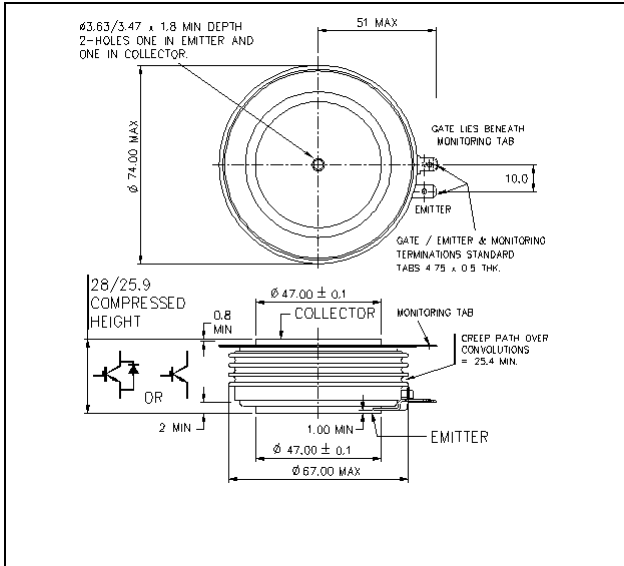


Figure 2 – 63mm \varnothing pole face

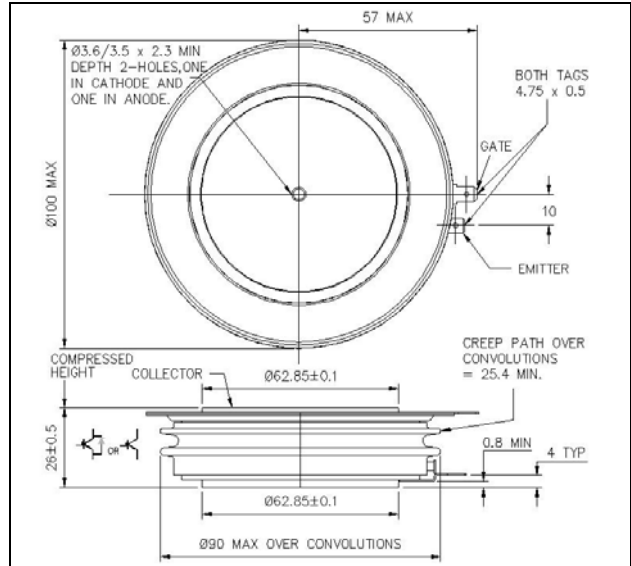


Figure 3 – 75mm \varnothing pole face

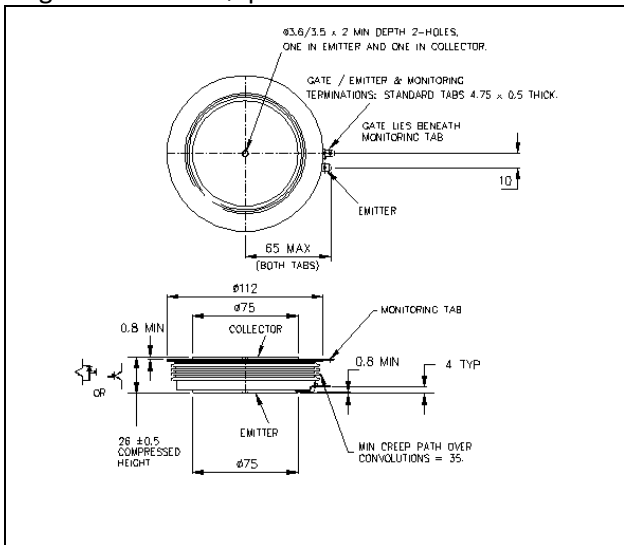


Figure 4 – 85mm \varnothing pole face

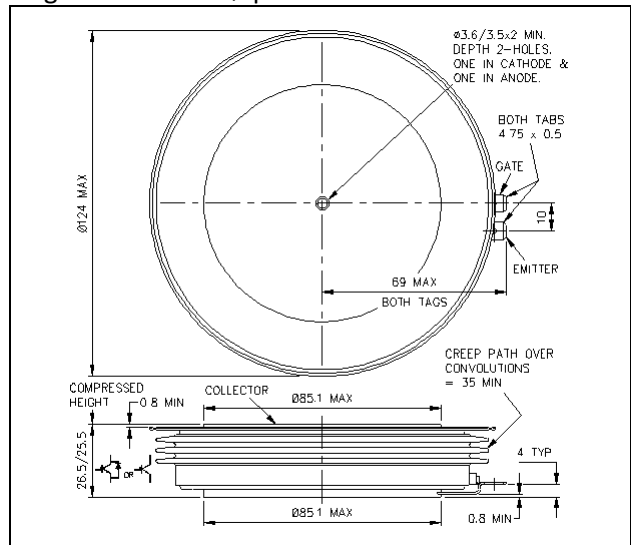


Figure 5 – 96mm \varnothing pole face

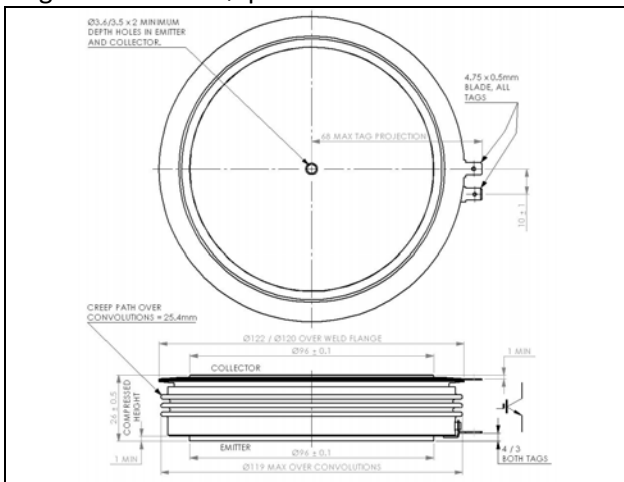
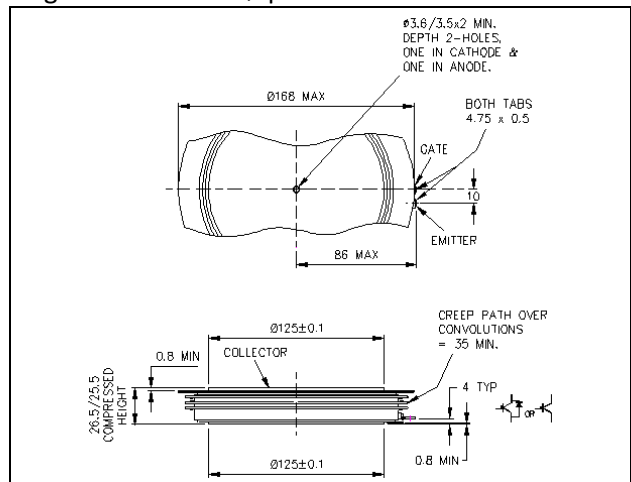


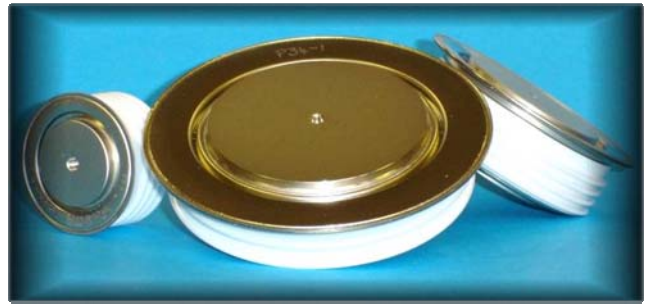
Figure 6 – 125mm \varnothing pole face



Third generation high power sonic-FRD

Improved safe operating area (SOA) and reverse recovery characteristics for both 2.5kV and 4.5kV HP-sonic monolithic diode range complements our new asymmetric IGBT range and also supports such applications as multi-level diode clamped converters

These diodes incorporate a unique manufacturing process and lifetime control to offer a class leading trade-off between conduction and switching losses. The wide SOA makes them ideal as freewheeling diodes for snubberless IGBT and IGCT applications



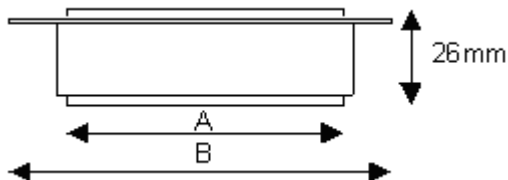
Features

- Robust dynamic characteristics – $di/dt > 4000A/\mu s$
- 150°C operating junction temperature
- Soft fast recovery – no snap off
- Low recovery losses, low forward voltage drop
- Snubberless operation

Applications

- Anti-parallel diodes of IGBT's and IGCT's
- Clamp and snubber diodes
- Any application which requires a fast low loss diode
- Ideally suited for:
 - Traction
 - Medium voltage drives
 - Renewables
 - Induction heating
 - Pulsed power applications

Type Part No.	V_{RRM} V	Dimensions	
		A mm	B mm
E0170YH40-45C	4000 - 4500	25	42
E0280YH20-25C	2000 - 2500	25	42
E0460QC40-45C	4000 - 4500	38	60
E0660NC40-45C	4000 - 4500	47	74
E0800QC20-25C	2000 - 2500	38	60
E1200NC20-25C	2000 - 2500	47	74
E1300VF40-45C	4000 - 4500	63	100
E2250VF20-25C	2000 - 2500	63	100
E2400TC40-45C	4000 - 4500	75	112
E4000TC20-25C	2000 - 2500	75	112



Certificate FM26085

IXYS UK Westcode Ltd's BS EN ISO9001 quality system is registered by BSI



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